

#### **Description**

The AOD2916 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

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#### TO-252-2L

#### **General Features**

 $V_{DS} = 100V I_{D} = 30A$ 

 $R_{DS(ON)}$  < 48m $\Omega$  @  $V_{GS}$ =10V

## **Application**

Battery protection

Load switch N-Channel MOSFET

Uninterruptible power supply

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AOD2916	TO-252-2L	HXY MOSFET	2500

#### Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	100	V	
Vgs	Gate-Source Voltage	e Voltage ±20		
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	30	Α	
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	13	А	
Ідм	Pulsed Drain Current <sup>2</sup>	80	А	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	30	mJ	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	42	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	3.6	°C/W	



## **Electrical Characteristics** (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	cteristic		1	l		
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
On Charac	cteristics					
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA	1.0	1.5	2.2	V
	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	37	48	mΩ
$R_{DS(on)}$	note3	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	39	55	mΩ
Dynamic (	Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	1964	-	pF
Coss	Output Capacitance		-	90	-	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	74	-	рF
Qg	Total Gate Charge	V <sub>DS</sub> =80V, I <sub>D</sub> =20A, V <sub>GS</sub> =4.5V	-	20	-	nC
$Q_gs$	Gate-Source Charge		-	3.1	-	nC
$Q_gd$	Gate-Drain("Miller") Charge	VGS-4.5V	-	14	-	nC
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-on Delay Time		-	11	-	ns
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =80V, I <sub>D</sub> =20A,	-	91	-	ns
$t_{\text{d(off)}}$	Turn-off Delay Time	$R_{G}$ =3.1 $\Omega$ , $V_{GS}$ =4.5 $V$	-	40	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	71	-	ns
Drain-Sou	rce Diode Characteristics and Maxim	um Ratings				
I.	Maximum Continuous Drain to Source Diode Forward				27	Α
Is	Current		-	-	21	А
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	Α
$V_{\text{SD}}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	_	1.2	V
trr	Body Diode Reverse Recovery Time	I -20A	-	64	-	ns
Qrr	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, dI/dt=100A/μs	-	152	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

- 2. EAS condition : TJ=25  $^{\circ}\text{C}$  ,VDD=50V,VG=10V,L=0.5mH,Rg=25 $\Omega$ ,IAS= 11A
- 3. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



# **Typical Performance Characteristics**

Figure1: Output Characteristics

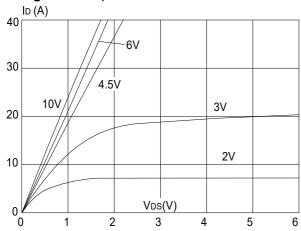


Figure 2: Typical Transfer Characteristics

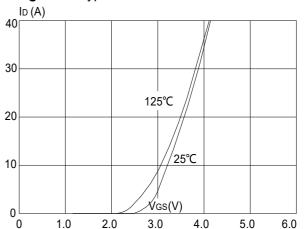


Figure 3:On-resistance vs. Drain Current

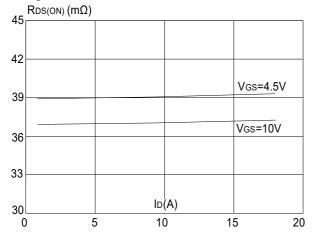


Figure 4: Body Diode Characteristics

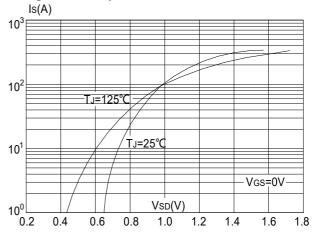


Figure 5: Gate Charge Characteristics

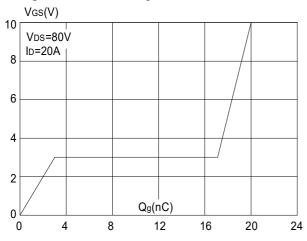
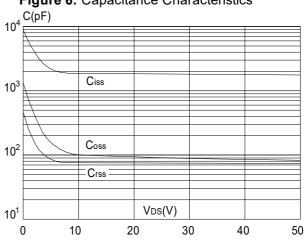


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

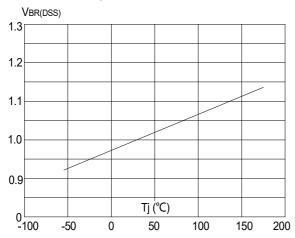
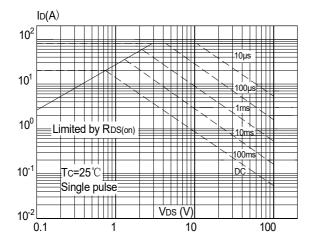
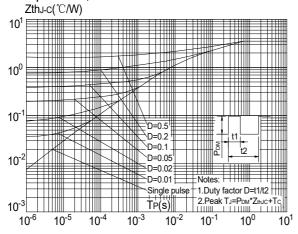


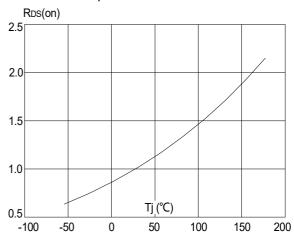
Figure 9: Maximum Safe Operating Area



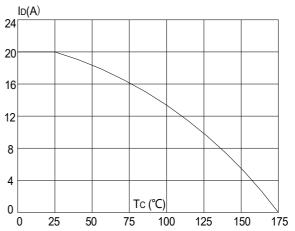
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



**Figure 8:** Normalized on Resistance vs. Junction Temperature

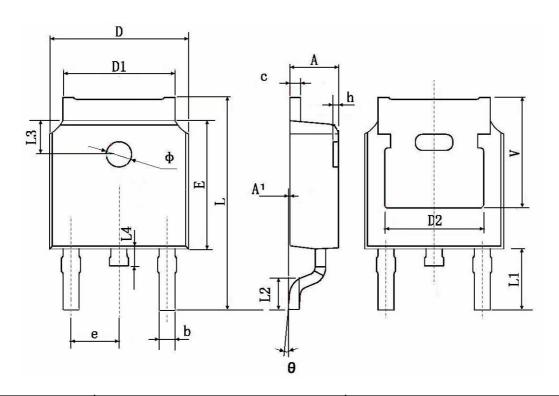


**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature





# **TO-252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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